

MPS
2364
STATIC READ
ONLY MEMORY
(8192x8)

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DESCRIPTION

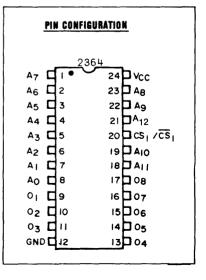
The 2364 high performance read only memory is organized 8192 words by 8 bits with access times of less than 350 ns. This ROM is designed to be compatible with all microprocessor and similar applications where high performance, large bit storage and simple interfacing are important design considerations. This device offers TTL input and output levels.

The 2364 operates totally asynchronously. No clock input is required. The programmable chip select input allows two 64K ROMS to be OR-tied without external decoding.

Designed to replace two 2732 32K EPROMS, the 2364 can eliminate the need to redesign printed circuit boards for volume mask programmed ROMS after prototyping with EPROMS.

- 8192 x 8 Bit Organization
- Single +5 Volt Supply
- Access Time 450 ns, 350 ns
- Completely TTL Compatible
- Totally Static Operation
- Three-State Outputs for Wire-OR Expansion
- One Programmable Chip Select
- Pin Compatible with 2716 & 2732 EPROM
- Replacement for Two 2732s
- 2716/2732 EPROMS Accepted as Program Data Inputs
 - 400mV Noise Immunity on Inputs

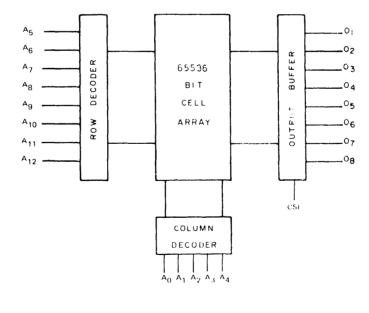
MXS 2364	' —	
		- FREQUENCY RANGE NO SUFFIX = 450ns A = 350ns
		 PACKAGE DESIGNATOR C = CERAMIC P = PLASTIC



NMOS

TIMING DIAGRAM ADDRESS INVALID VALID INVALID INPUTS CHIP SELECT DISABLED ENABLED | DISABLED tco -DATA HIGH HIGH INVALID VALID INVALID OUTPUTS IMPEDANCE IMPEDANCE - 1ACC -







ABSOLUTE MAXIMUM RATINGS

Ambient Temperature under Bias Storage Temperature -65°C to +70°C -65°C to +150°C Supply Voltage to Ground Potential Applied Output Voltage -0.5V to +7.0V -0.5V to +7.0V Power Dissipation -0.5V to +7.0V

COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

D. C. CHARACTERISTICS (TA = 0 C to +70 C, V_{CC} = 5.0V ± 5%, unless otherwise specified)

Parameter	Min.	Max.	Units	Test Conditions
Power Supply Current		100	mA	$V_{IN} = V_{CC}, V_0 = Open, T_A = 0^{\circ}C$
Power Supply Current		95	mΑ	$V_{IN} = V_{CC}, V_0 = Open, T_A = 25^{\circ}C$
Output Leakage Current		10	μΑ	Chip Deselected, $V_0 = 0$ to V_{CC}
Input Load Current		10	μA	VCC = Max. VIN = 0 to VCC
Output Low Voltage		0.4	Volts	$V_{CC} = Min. I_{OL} = 2.1 mA$
Output High Voltage	2.4		Volts	$V_{CC} = Min. I_{OH} = -400 \mu A$
Input Low Voltage	-0.5	0.8	Volts	See Note 1
Input High Voltage	2.0	VCC+1	Volts	
	Power Supply Current Power Supply Current Output Leakage Current Input Load Current Output Low Voltage Output High Voltage Input Low Voltage	Power Supply Current Power Supply Current Output Leakage Current Input Load Current Output Low Voltage Output High Voltage Input Low Voltage -0.5	Power Supply Current Power Supply Current Output Leakage Current Input Load Current Output Low Voltage Output High Voltage Input Low Voltage Output Low Voltage Output High Voltage Output Low Voltage	Power Supply Current Power Supply Current Power Supply Current Output Leakage Current Input Load Current Output Low Voltage Output High Voltage Input Low Voltage Output Low Voltage Output Low Voltage Output High Voltage Output Low Voltage

A. C. CHARACTERISTICS (T_A = 0 C to +70 C. V_{CC} = 5.0V \pm 5%. unless otherwise specified)

		2364		2364A			
Symbol	Parameter	Min.	Max.	Min.	Max.	Units	Test Conditions
tACC	Address Access Time		450		350	ns	
tco	Chip Select Delay		200		200	ns	
tDF	Chip Deselect Delay		175		175	ns	See Note 2
tOH	Previous Data Valid After Address Change Delay	40		40		ns	

CAPACITANCE $(T_A = 25 \text{ C}, f = 1.0 \text{MHz}, \text{See Note 3})$

Symbol	Parameter	Min.	Max.	Units	Test Conditions
CIN	Input Capacitance		8	рF	All Pins except Pin under
COUT	Output Capacitance		10	pF	Test Tied to AC Ground

Note 1: Input levels that swing more negative than -0.5V will be clamped and may cause damage to the device.

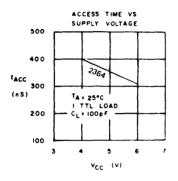
Note 2: Loading 1 TTL + 100 pF, input transition time: 20 ns

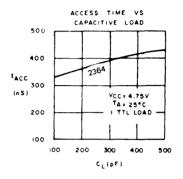
Timing measurement levels: input 1.5V, output 0.8V and 2.0V. $C_{\parallel}=100~\mathrm{pF}$

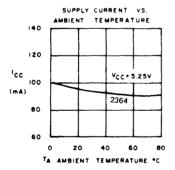
Note 3: This parameter is periodically sampled and is not 100% tested.

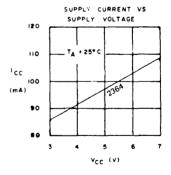


TYPICAL CHARACTERISTICS









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